

Calibration of APTS Prototypes Developed in 65 nm CMOS Imaging Technology

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Overview of the project

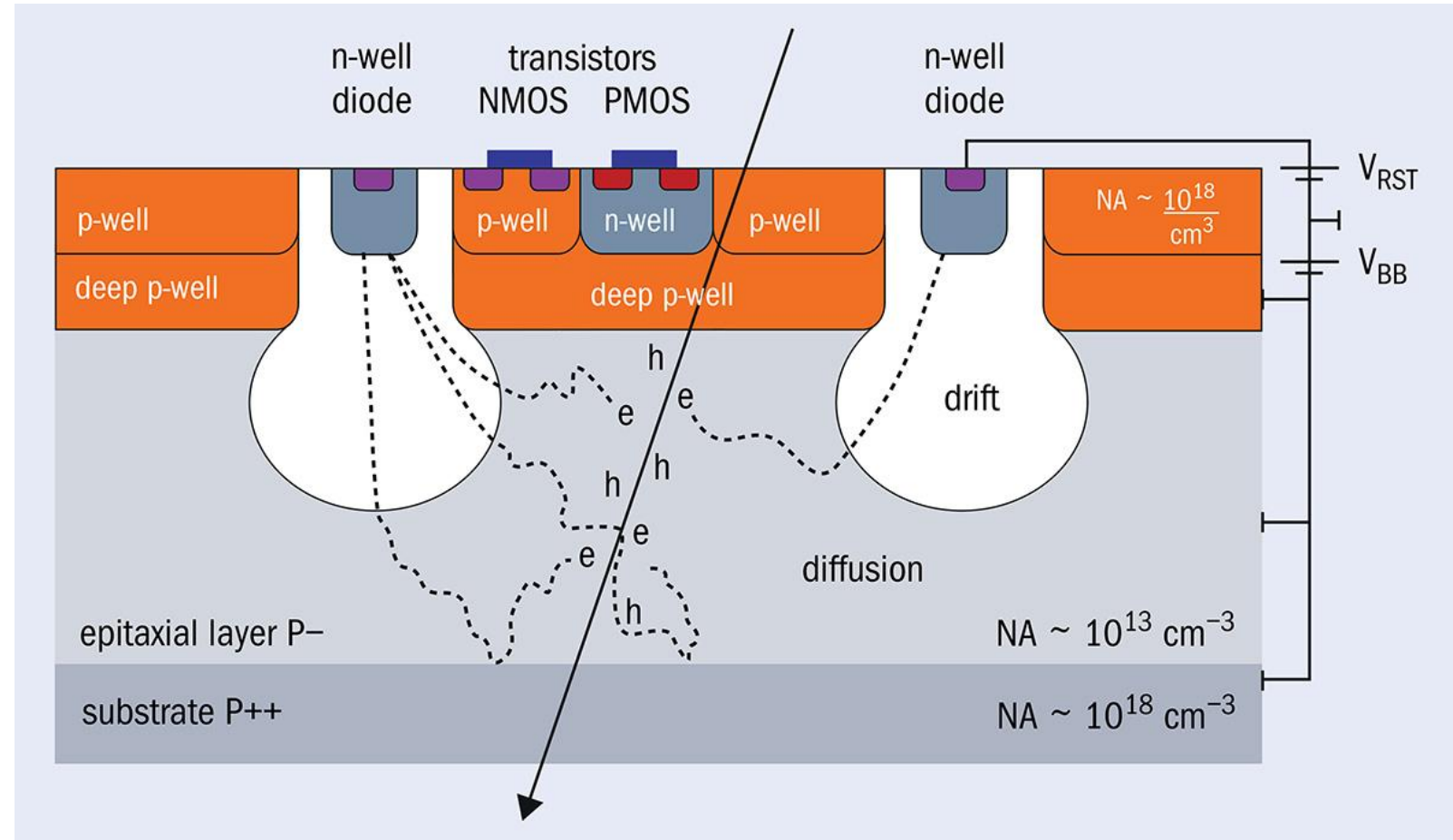
- Laboratory Characterization of Monolithic Active Pixel Sensors (MAPS)

Summary of main steps:

- Waveform Analysis
- Gain Characterization
- Charge Calibration Using Fe-55 Source
- Getting the Calibration Curve

MAPS Detectors

- CMOS: Complementary Metal-Oxide Semiconductor
- A charged particle or X-ray in Si creates e^-/h^+ pairs.
- Depleted region steers e^- to the n-well diode (fast drift); the rest comes by diffusion.
- In-pixel CMOS electronics turn the collected charge into a signal level.

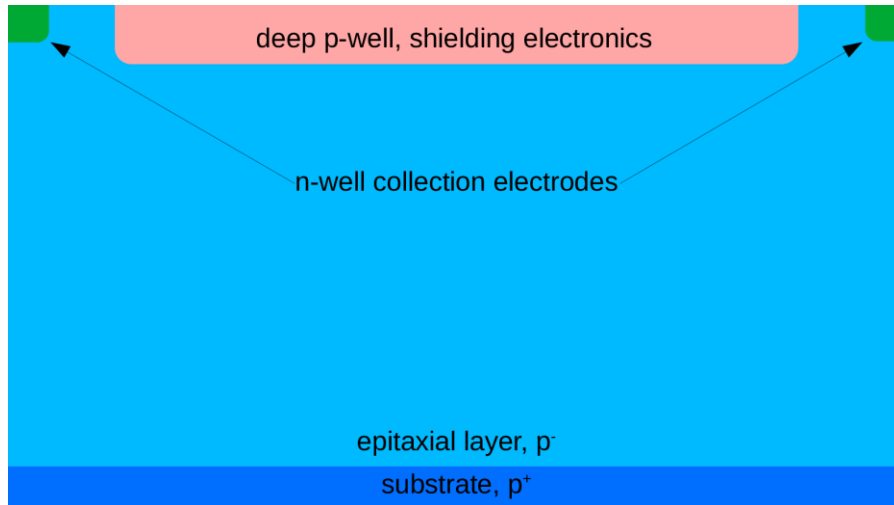


We need a calibration to express signals in meaningful physical units and map per-pixel gain/charge differences, to have a clearer picture of the detector's behavior.

MAPS Layouts

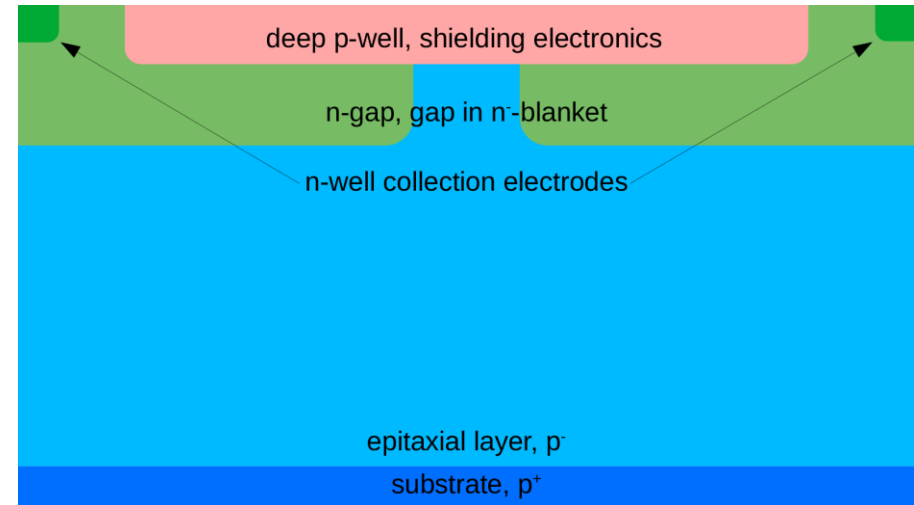
Standard

- Slow Charge Collection
- More shared charge (Higher Spatial Resolution)
- Low efficiency at High Thresholds



N-Gap

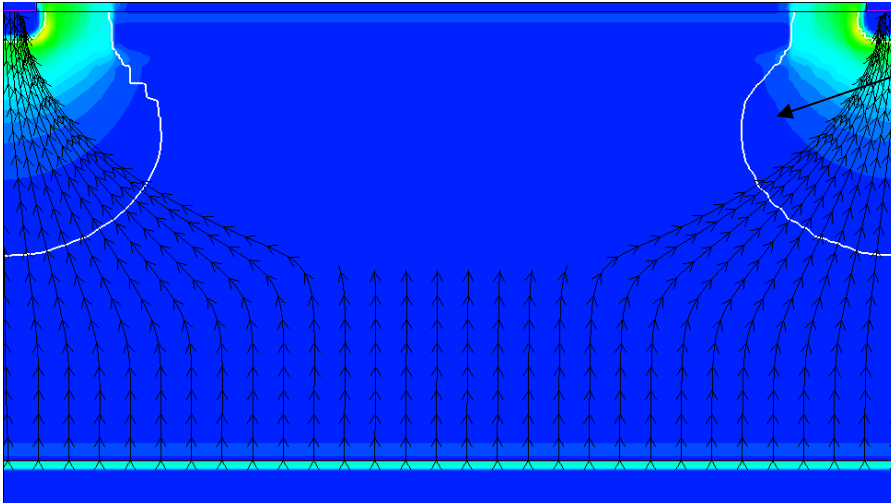
- Fast Charge Collection
- Less shared charge (Lower Spatial Resolution)
- High efficiency at High Thresholds



MAPS Layouts

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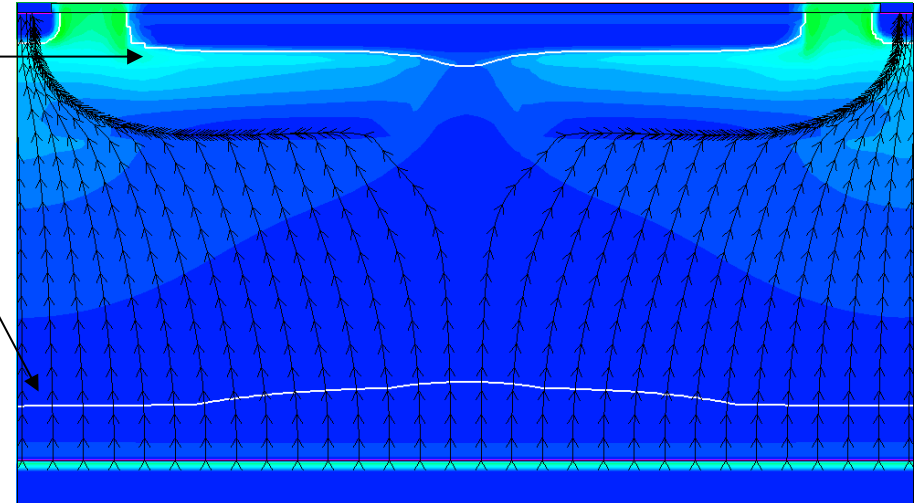
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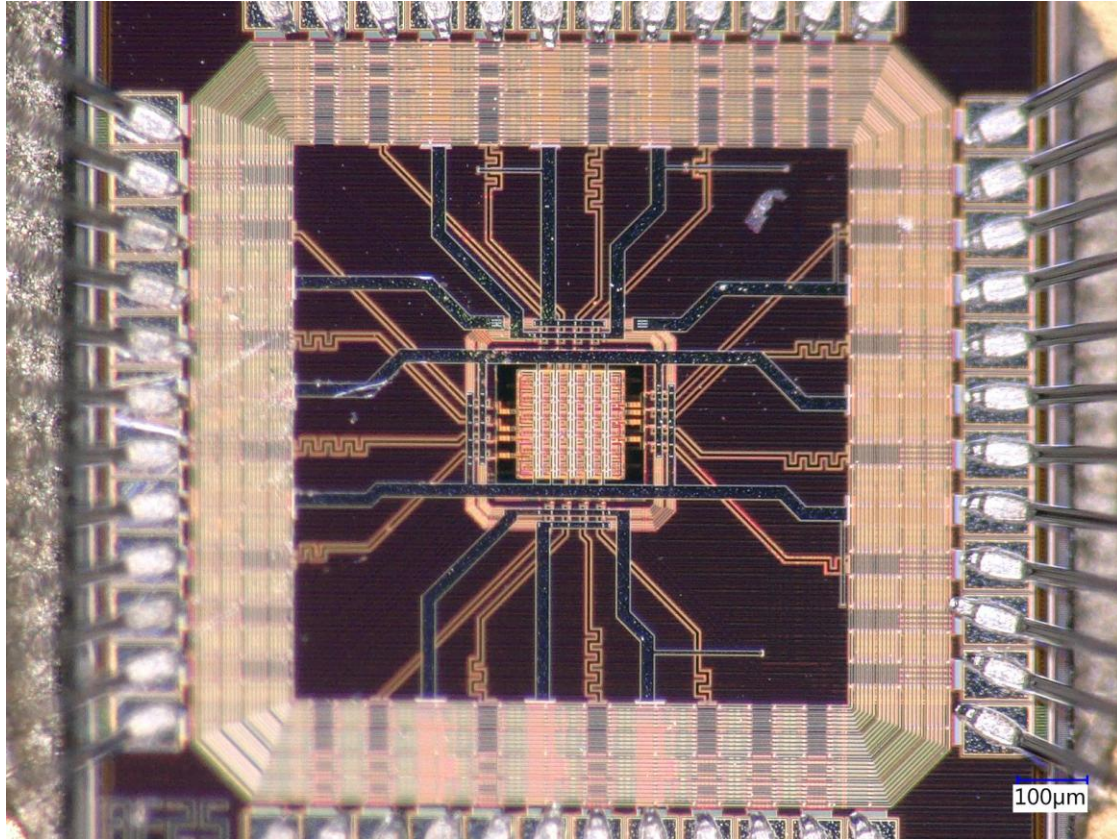
N-Gap

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Depleted
Region

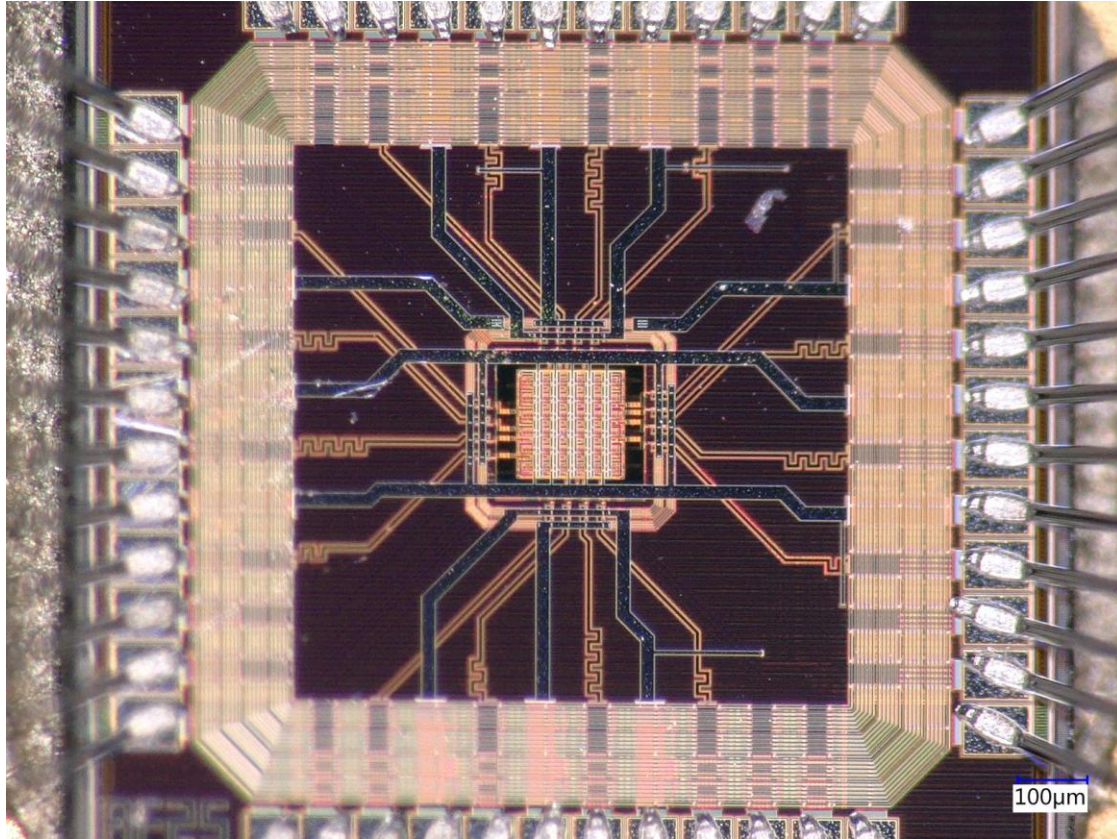


Details of APTS Chip ID 27



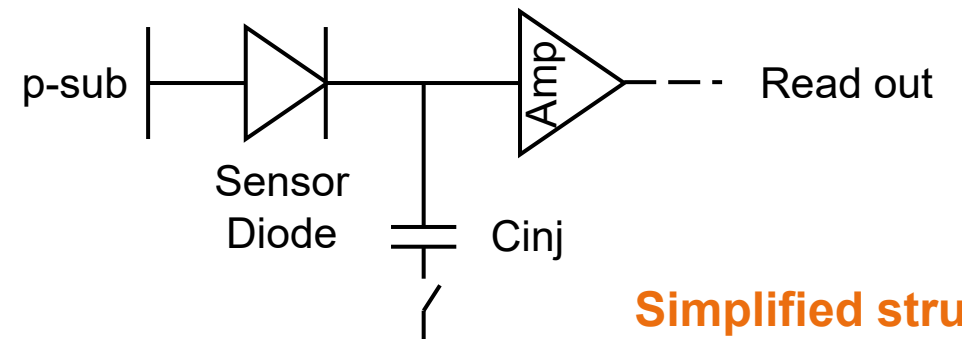
- Layout: N-Gap
- Gap Size: 2.5 μm
- Die size: 1.5 mm $\times$ 1.5 mm
- Matrix: 6 $\times$ 6 pixels
- Readout: Direct analogue of central 4 $\times$ 4 pixels
- Pixel Pitch 15 μm $\times$ 15 μm

Details of APTS Chip ID 27



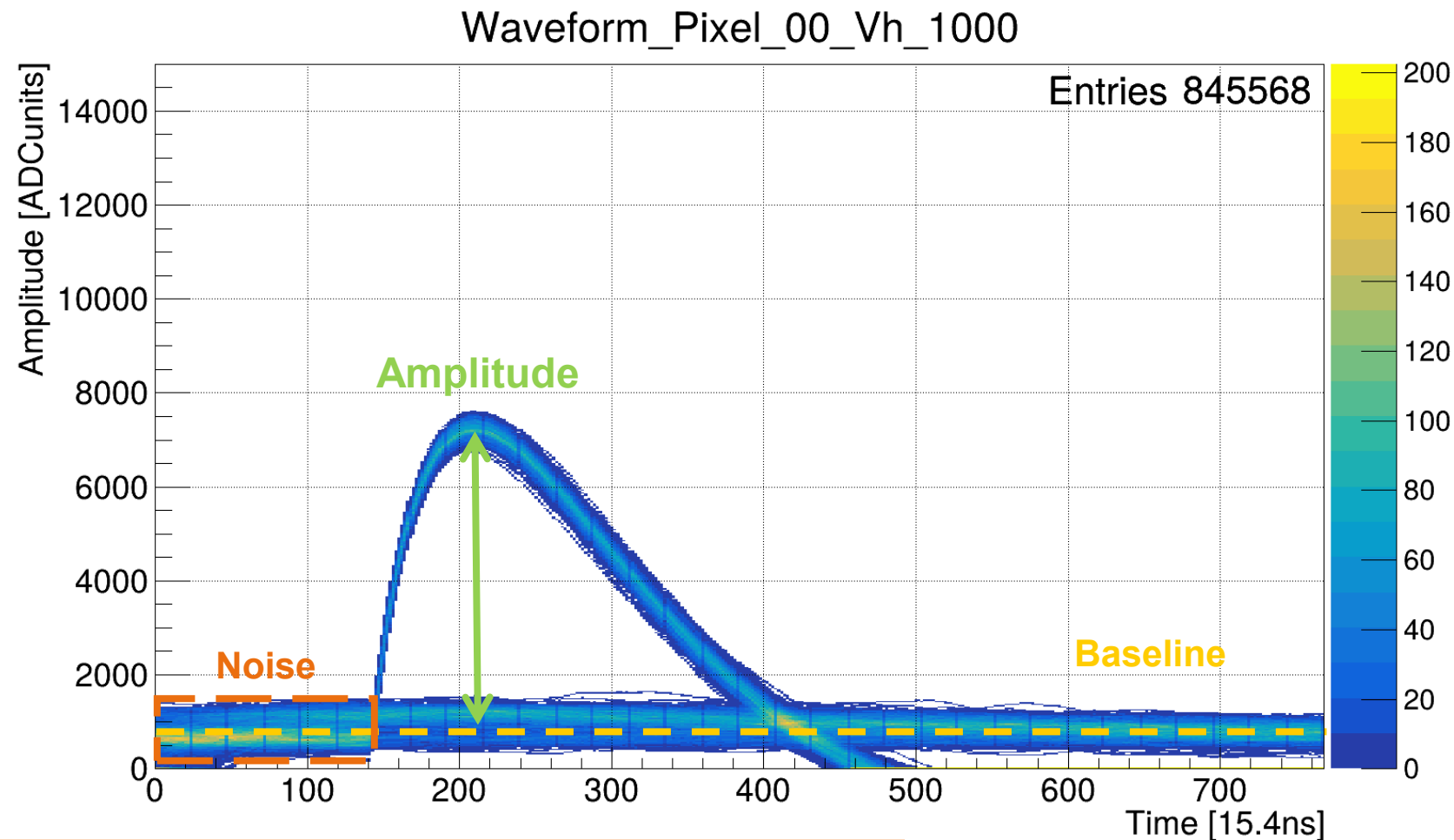
From diode to analog voltage

- The diode collects electrons and makes a small voltage step on the pixel node.
- A tiny amplifier copies/boosts that voltage to the analog output.
- A gentle reset current brings the node back to baseline after the pulse.
- For tests, a small injection capacitor (C_{inj}) can fake a hit with a voltage step



**Simplified structure
of the electronics**

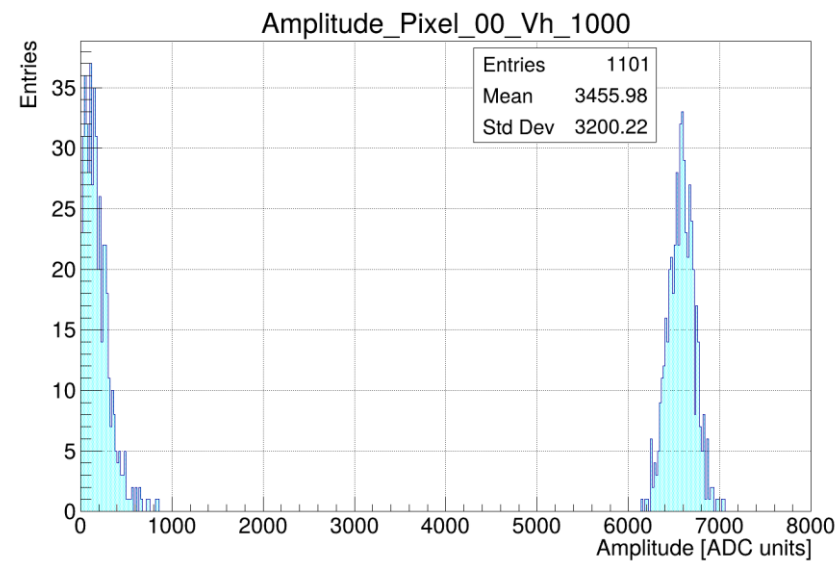
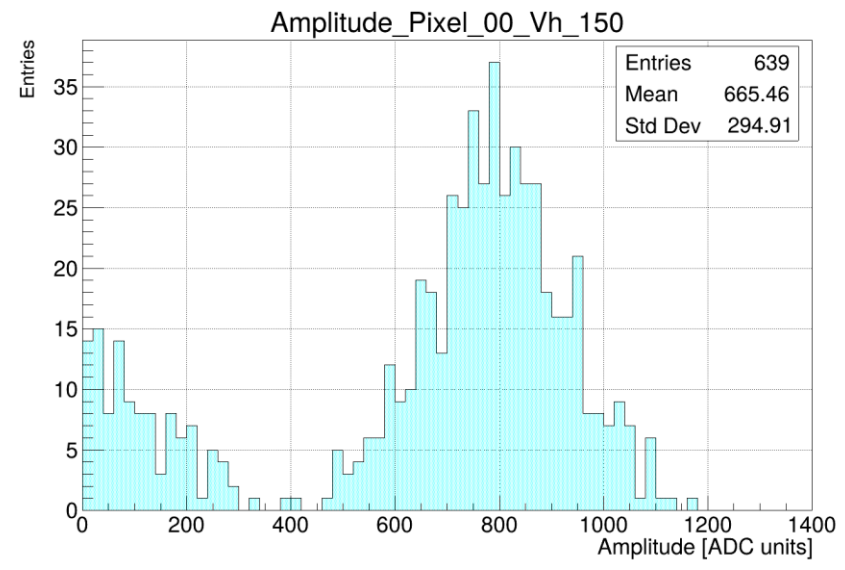
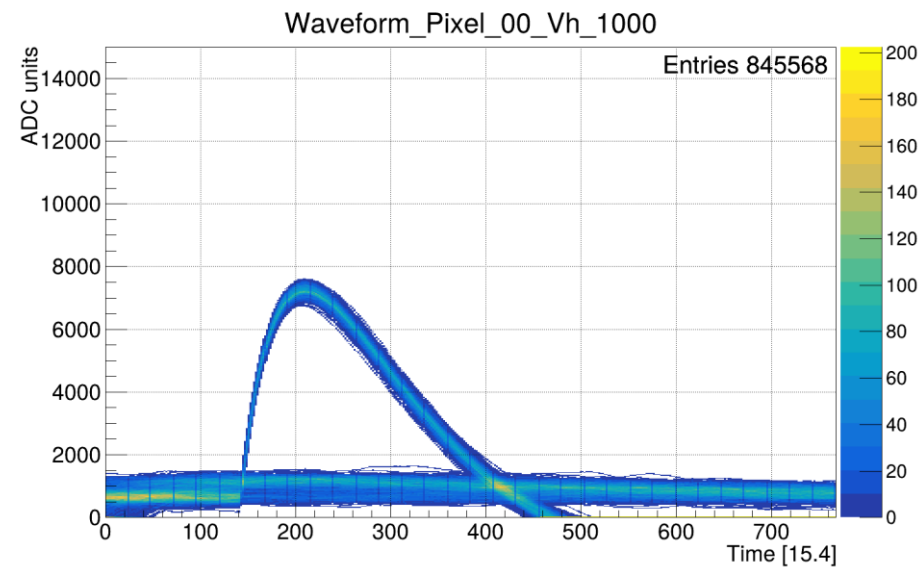
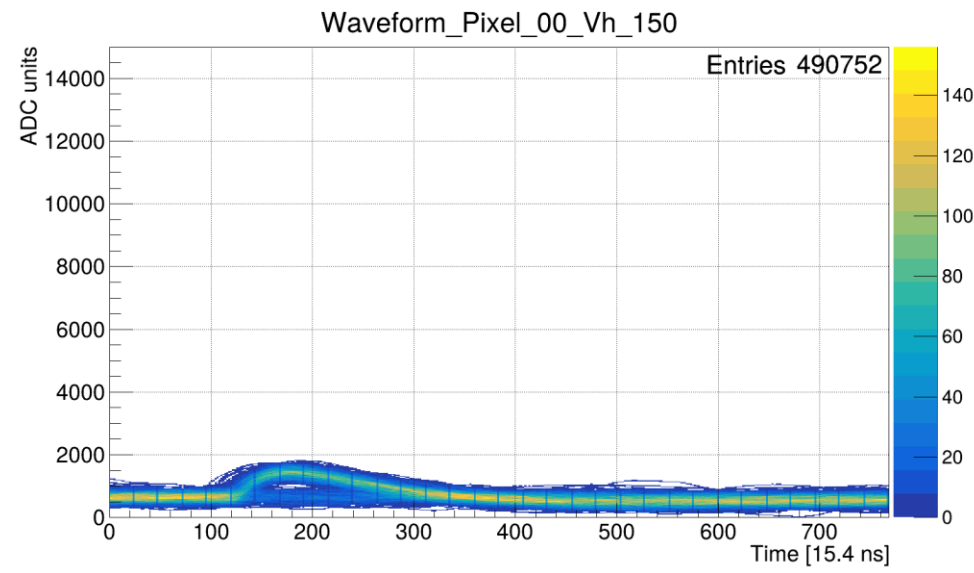
Waveform Analysis



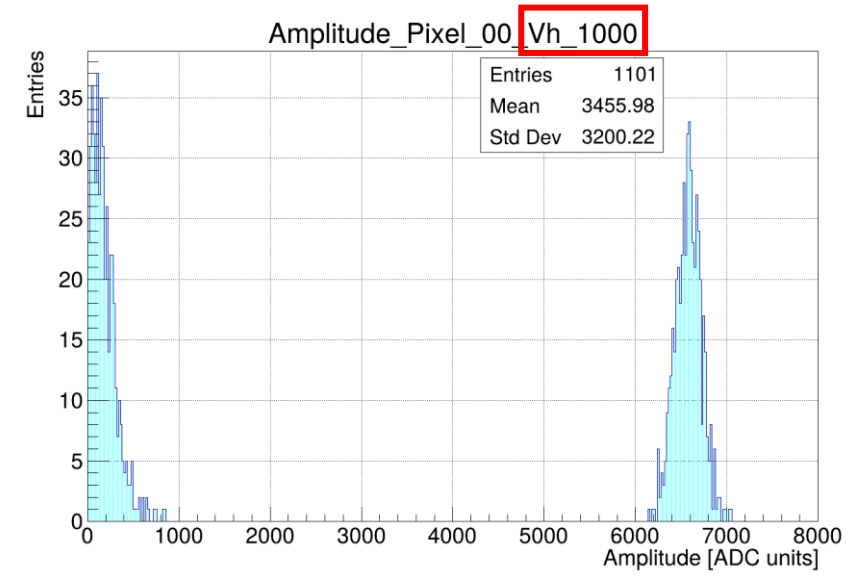
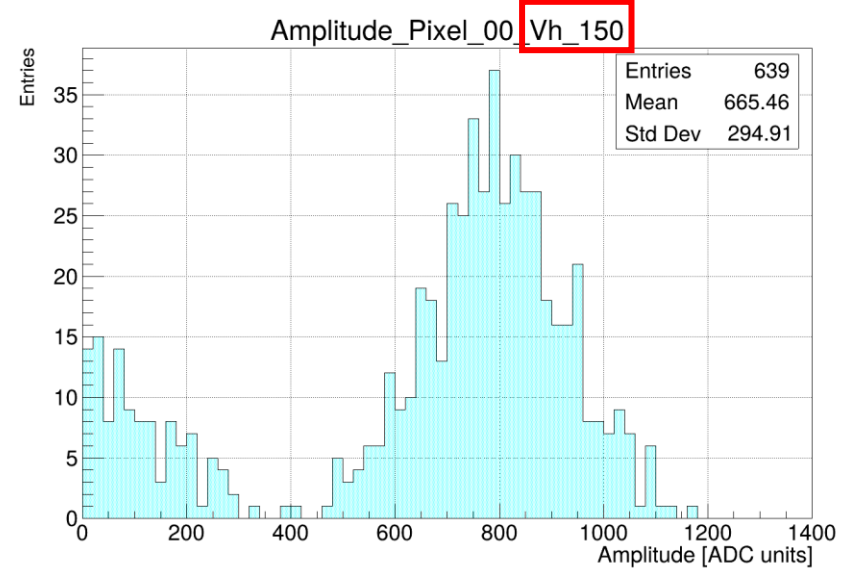
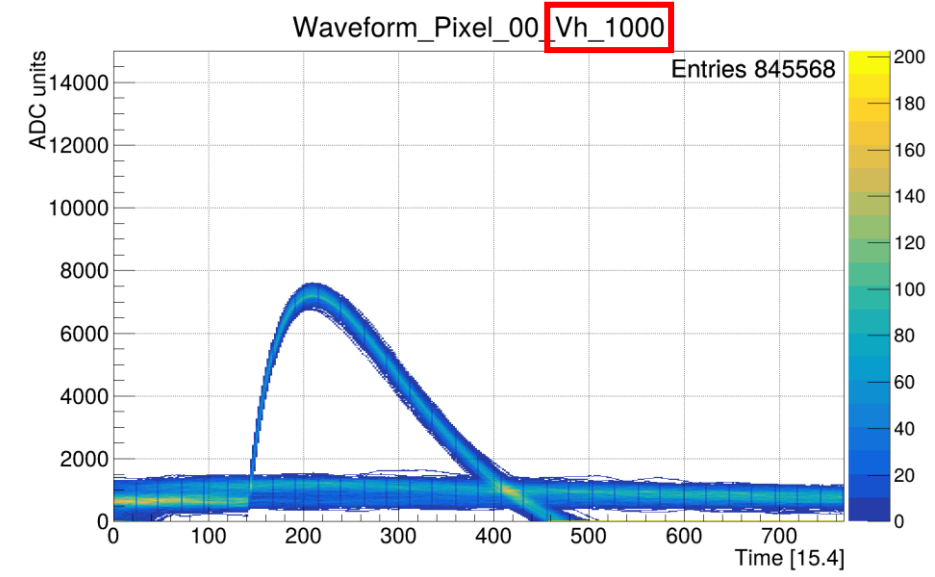
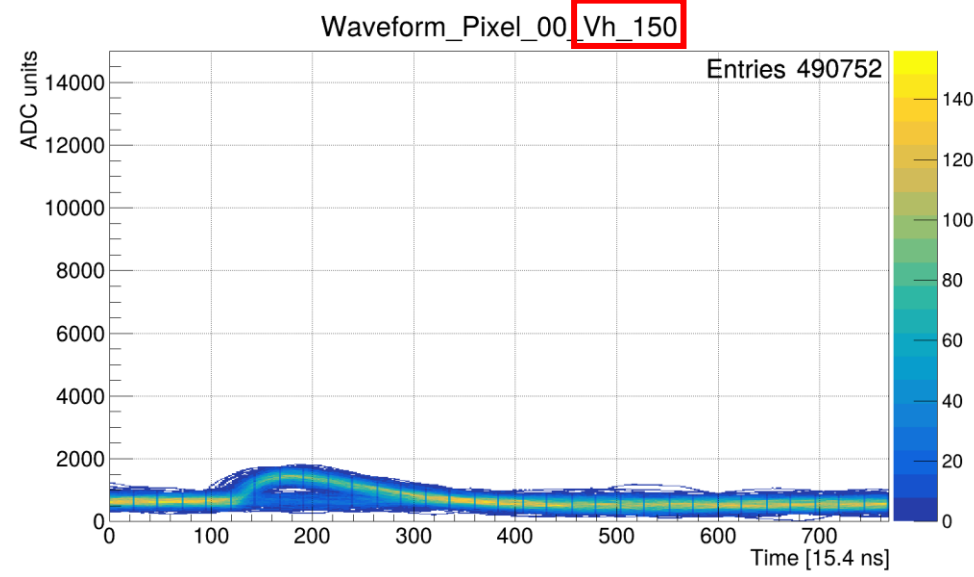
- Baseline (BL): Mean of pre-signal samples; used to remove DC offsets per waveform.
- Noise (σ): RMS fluctuation around BL; higher σ means harder hit discrimination.
- Amplitude (A): Peak height above BL ($\text{Max} - \text{BL}$) in ADC counts.
- S/N: Ratio of signal strength to noise (A/σ); higher is better.
- ADC: Analog-to-Digital Converter; digitizes the analog voltage into discrete counts.

• **Voltage test-pulse scan: 0 $\rightarrow$ 1200 mV in 10 mV steps.**

Behavior of Waveforms at High and Low Amplitude Test Pulse



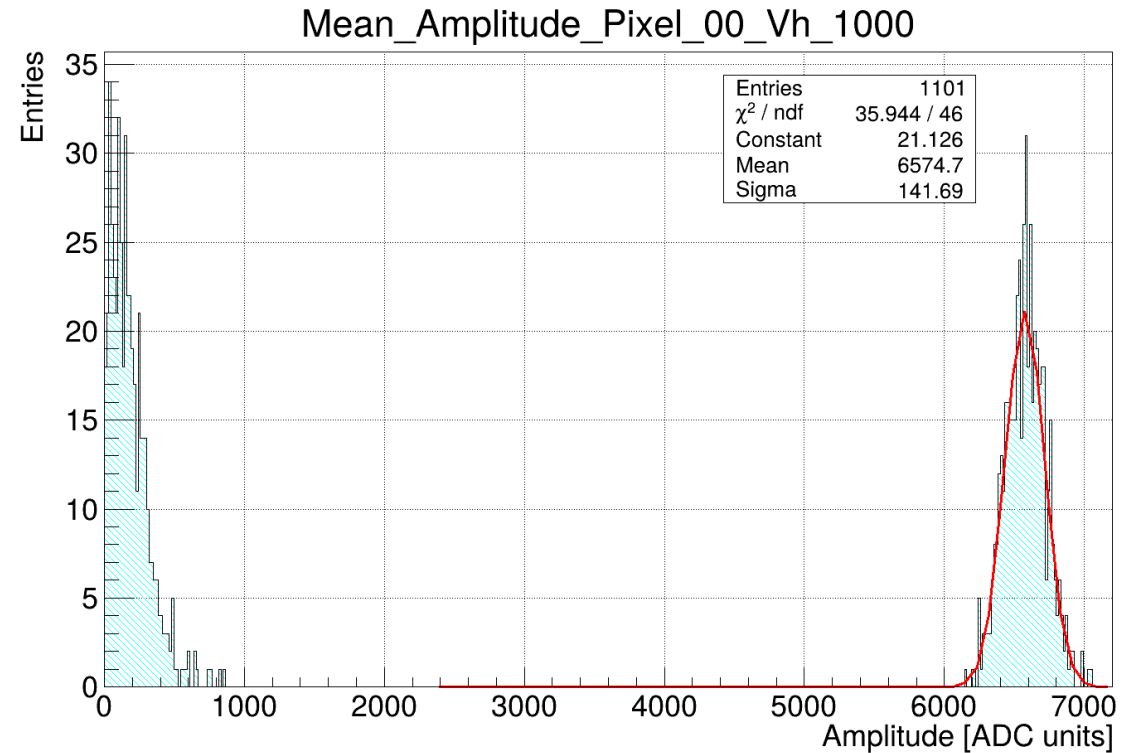
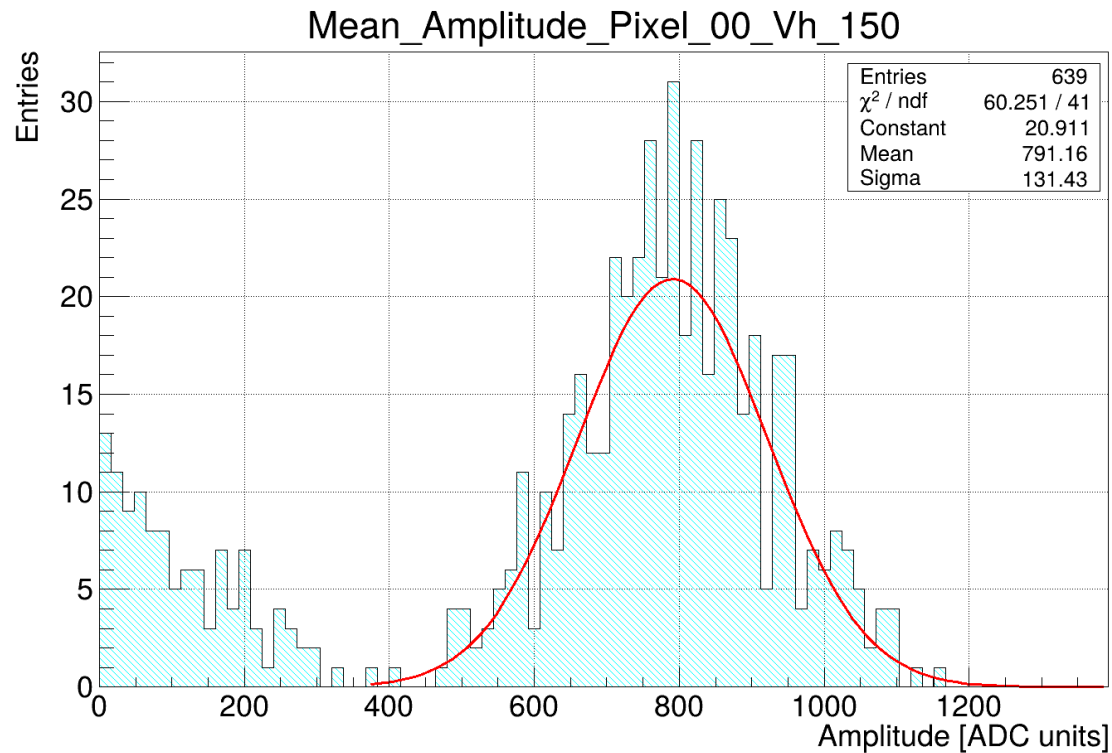
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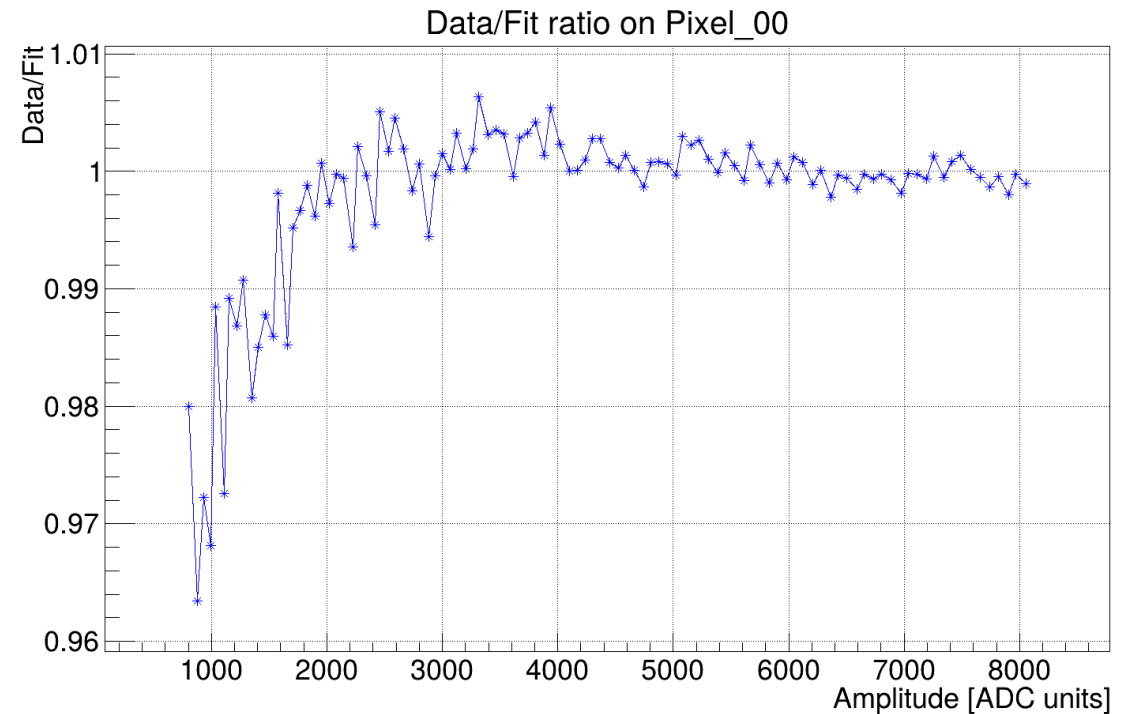
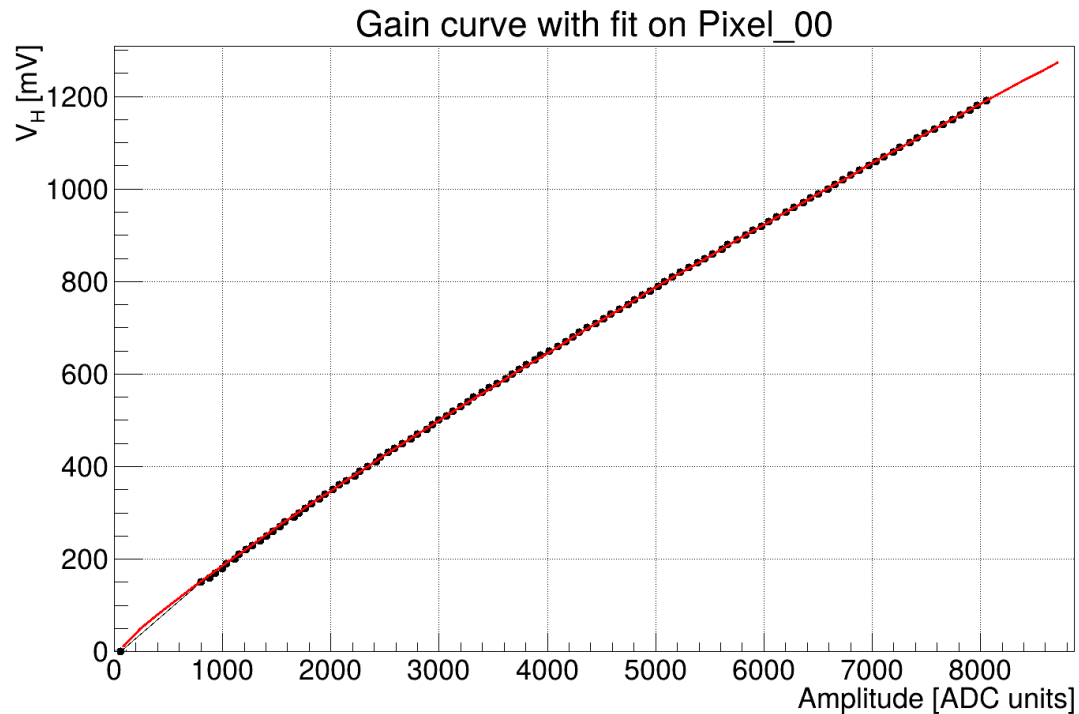
How did we get the elements for our Gain curve

Robust mean extraction: quantile-centered Gaussian fit

- **Fix:** Use a quantile (e.g., $q = 0.8$) as the initial fit center.
- **Window:** Fit a Gaussian in a $\pm 2\sigma$ window around that center.



Gain curve



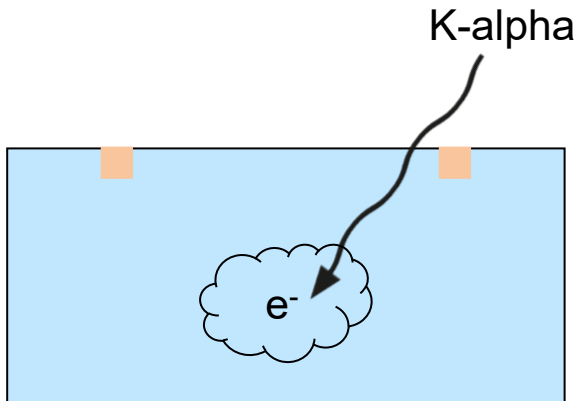
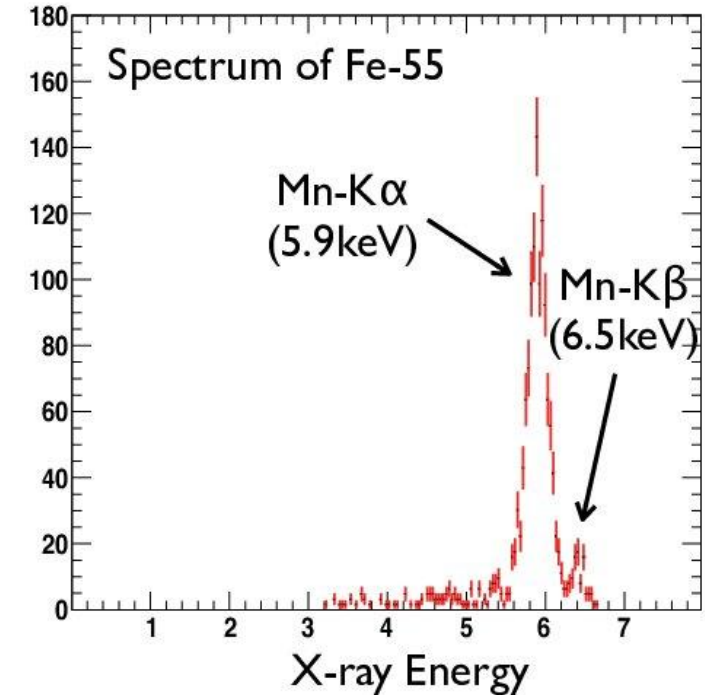
- We obtained a **per-pixel mapping** of how amplitude grows with test pulses:
 $V_H = g(x)$, where x = average waveform **amplitude (ADC counts)** and x_0 the mean of the Baseline.
- We use a **stable empirical function** where the **gain curve in VH units** is ready for charge calibration.

$$V_H = (p_0(x - x_0) + p_1|x - x_0|^{0.5}) \times (p_2x + p_3),$$

Charge Calibration Using Fe-55 Source

Why use Fe-55?

- Fe-55 is a **stable, low-rate X-ray source** that decays by **electron capture** to Mn-55.
- The Mn emits **characteristic X-rays**, mainly **K- α** (~5.9 keV) and a smaller **K- β** (~6.49 keV) line.
- These X-ray energies are **narrow and repeatable**, giving a **known deposited energy**—perfect to define an absolute charge scale.



What happens in silicon?

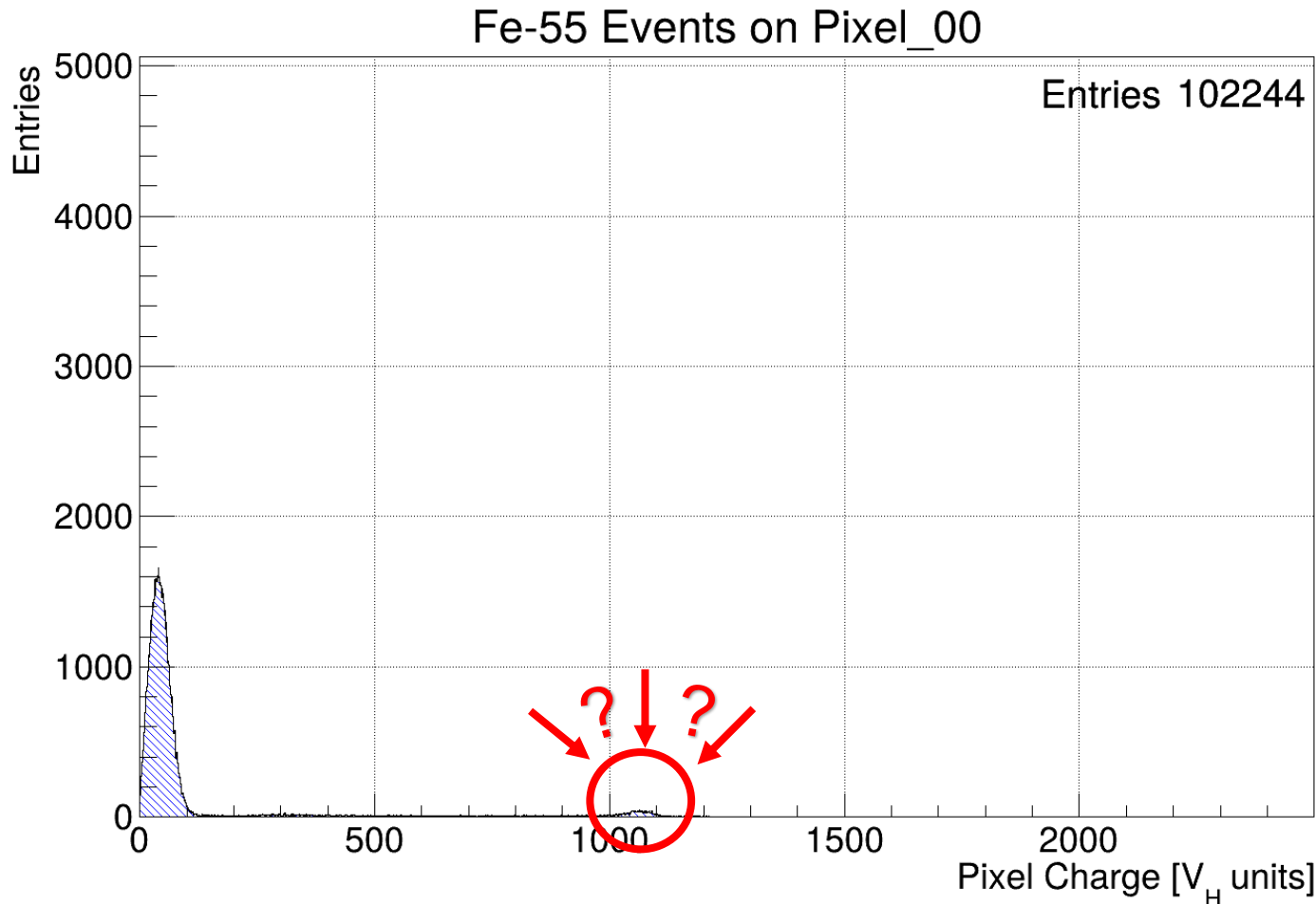
- A 5.9 keV (K- α) X-ray is absorbed creating a **localized cloud of electron–hole pairs**.
- In silicon, it takes about **3.6 eV** to make one **e–h pair**; in our calibration we use **K- α $\approx$ 1609 electrons** as the reference charge.

Fe-55 Source Data-Acquisition Setup

- Setup: Place the Fe-55 source in front of the sensor.
- Data: ~124k events acquired; raw files processed with corryvreckan.

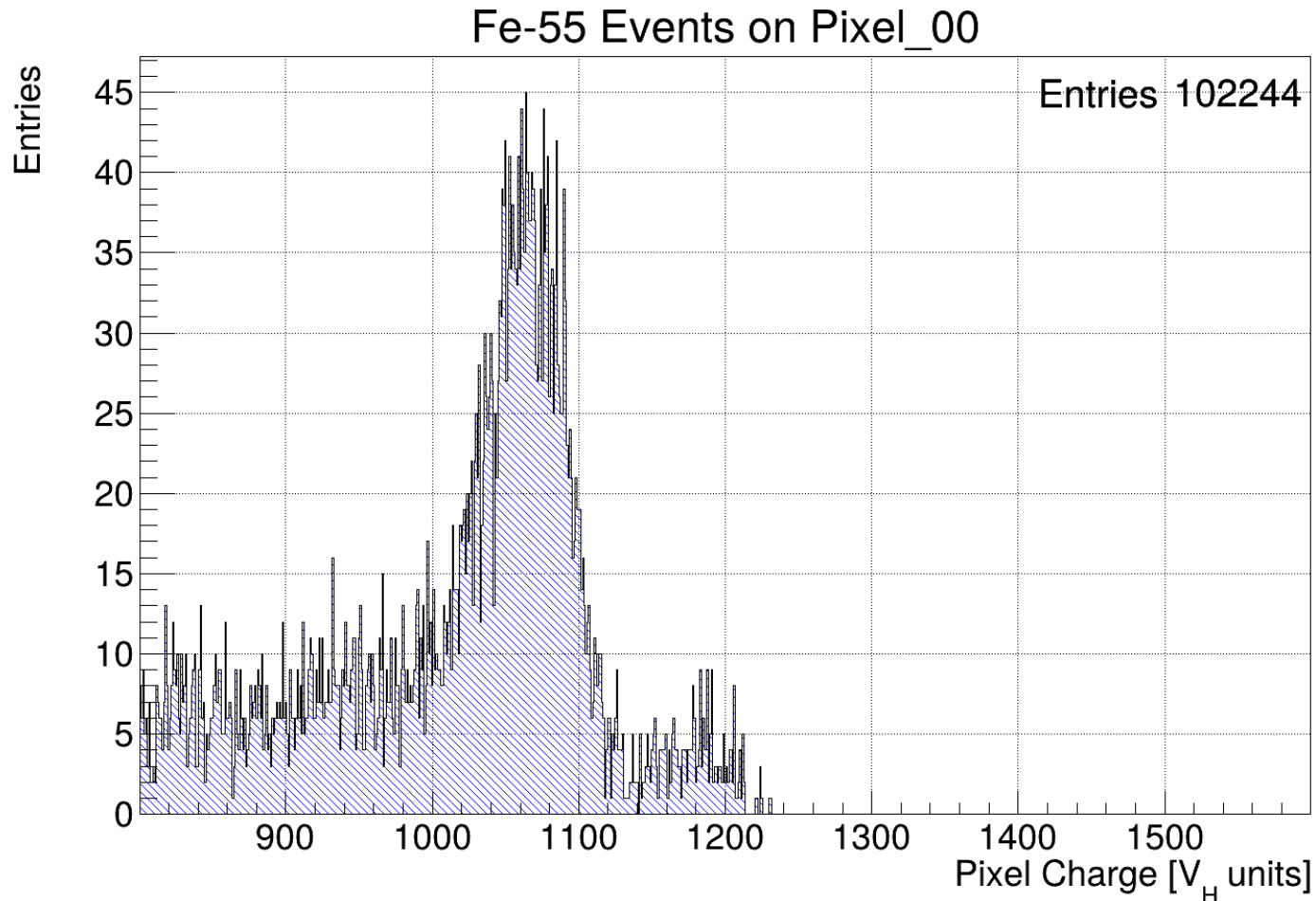


Charge Calibration Using Fe-55 Source



- Per pixel, we build **amplitude histograms in Amplitude test pulse units**.
- Identify the **K- α peak** in the Fe-55 spectrum.
- **Known charge:** K- $\alpha \approx 1609 e^-$ in silicon.
- **Gaussian fit** $\rightarrow$ Peak mean $\mu_{K-\alpha}$ (in **Amplitude test pulse units**) per pixel.
- **Scale factor** $S = 1609 / \mu_{K-\alpha}$.
- **Converts to electrons:**
$$e^- = S \times (p_0(x - x_0) + p_1|x - x_0|^{0.5}) \times (p_2x + p_3)$$
- **Result:** A **charge calibration curve in electron units**, comparable across pixels.

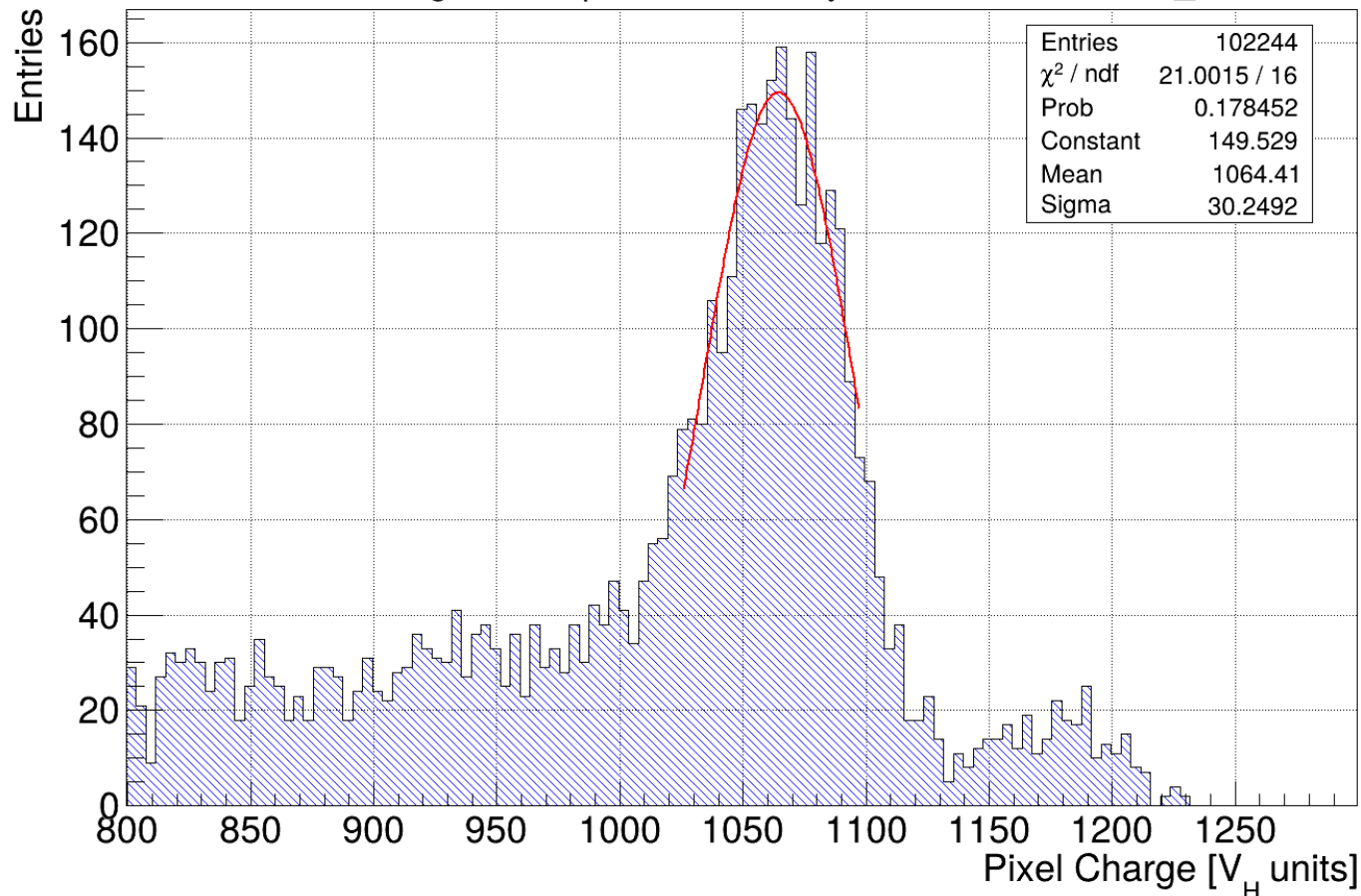
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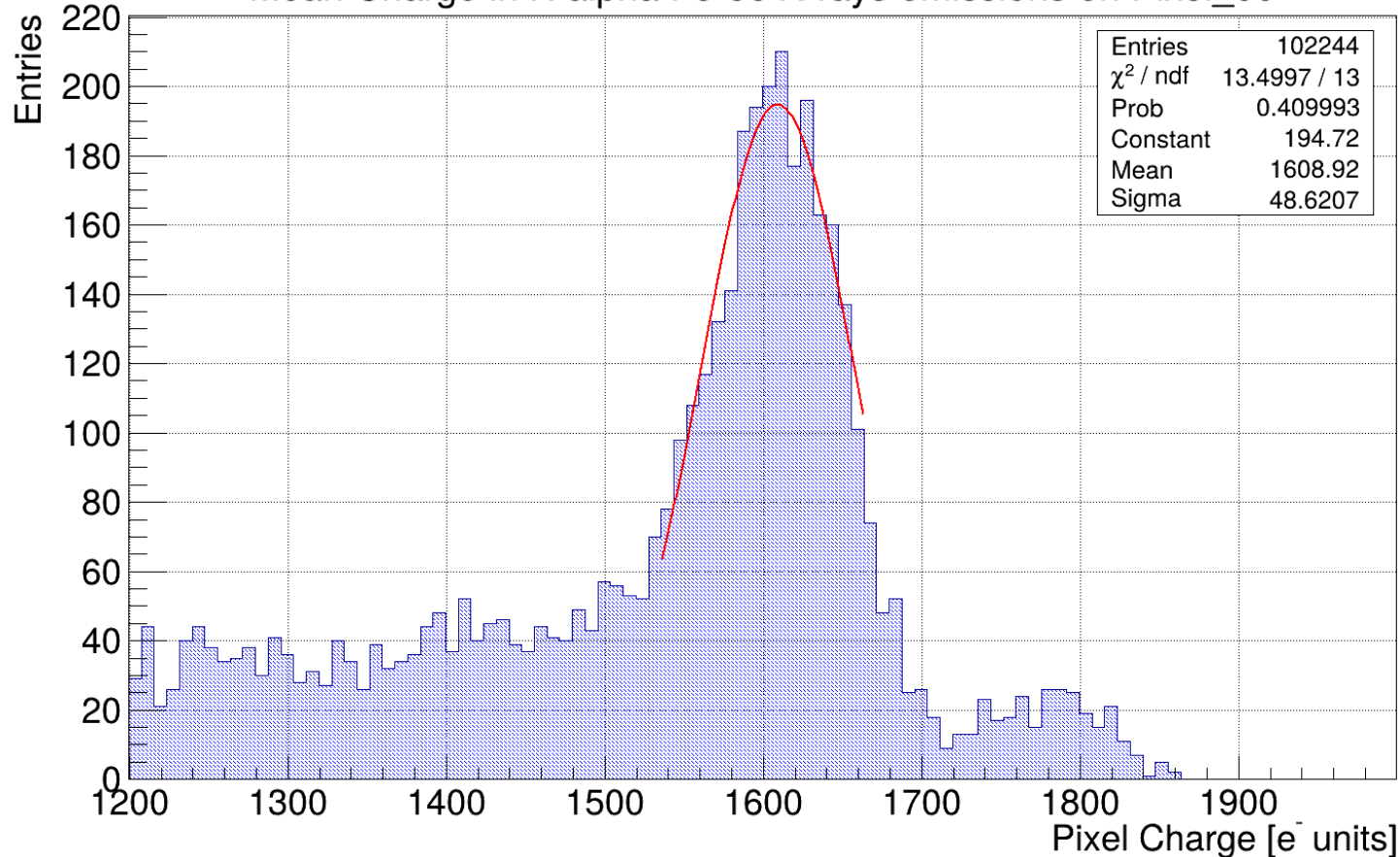
Mean Charge in K-alpha Fe-55 X-rays emissions on Pixel_00



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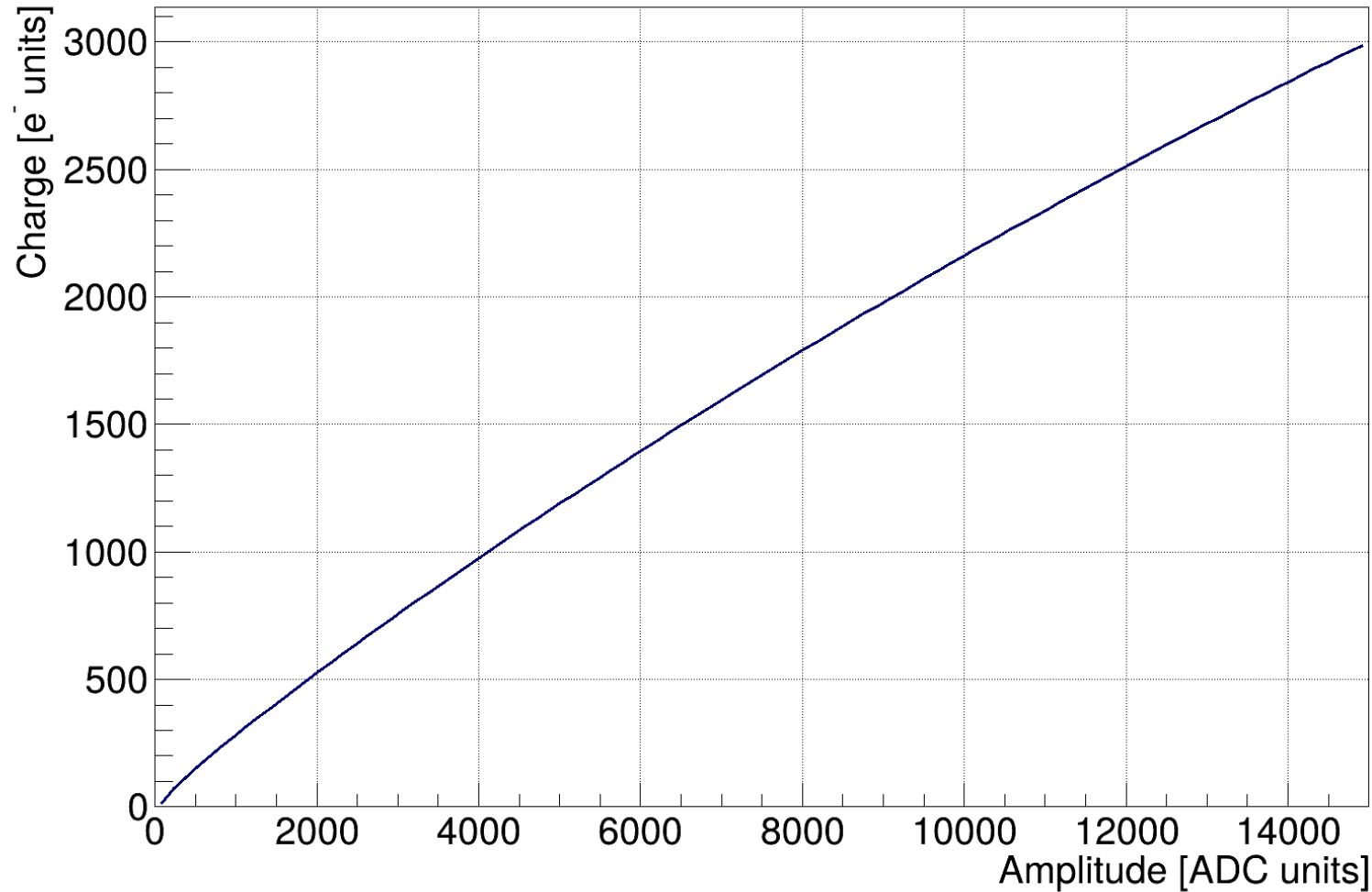
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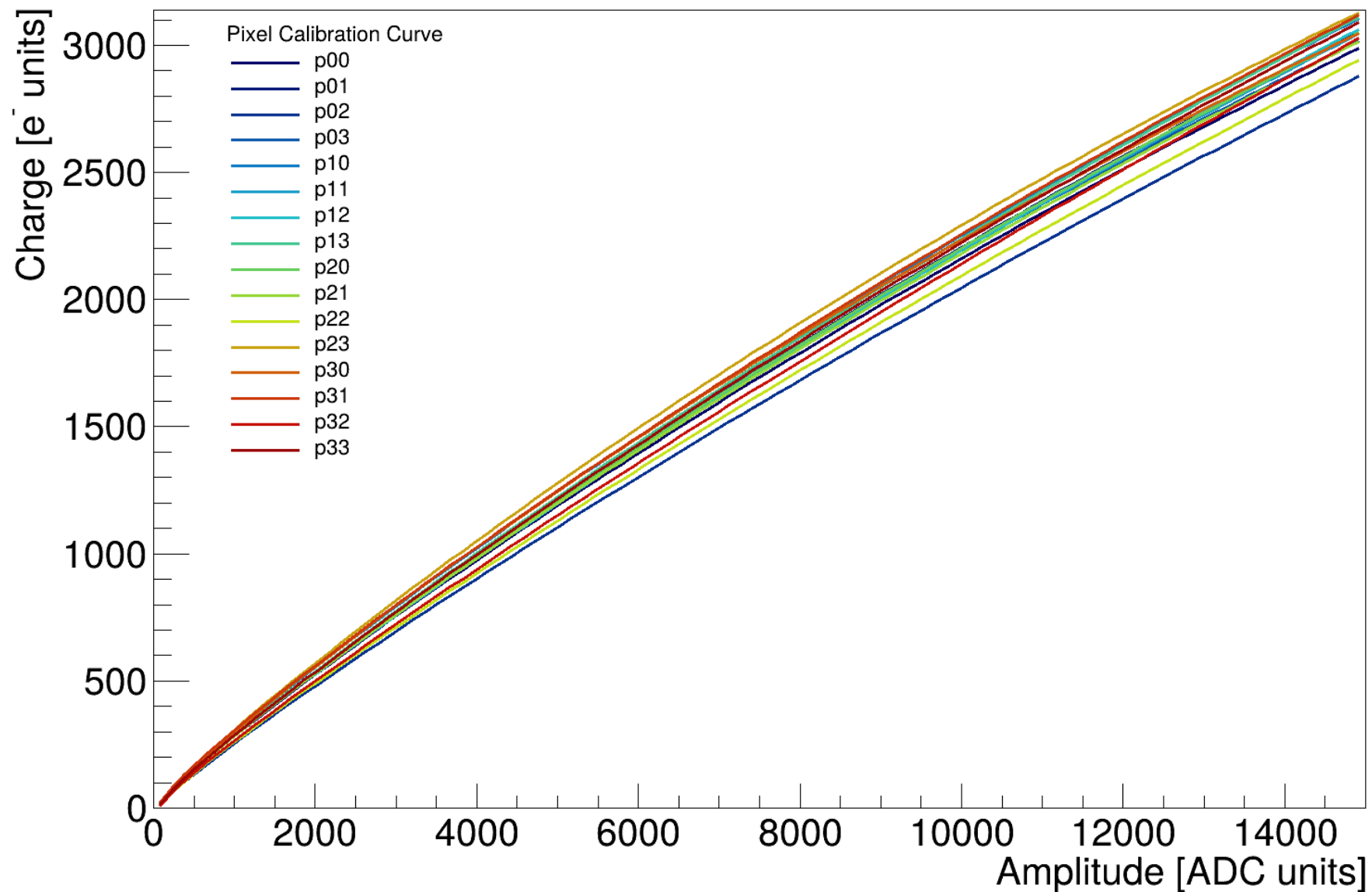
Example of calibration curves

Calibration curve Pixel_00

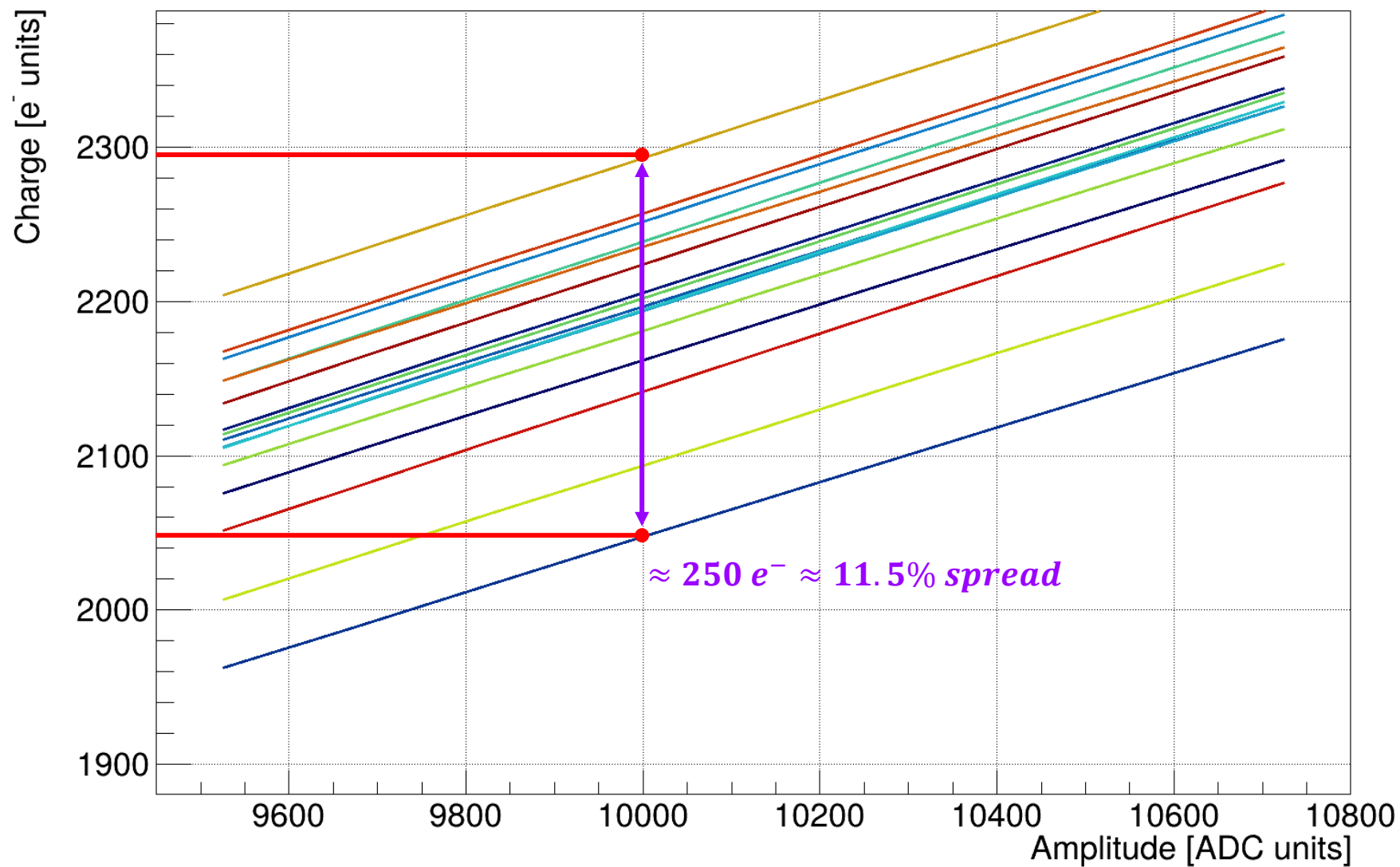


$$e^- = S \times (p_0(x - x_0) + p_1|x - x_0|^{0.5}) \times (p_2x + p_3),$$

Calibration Curves of all the Pixels



Difference between Highest and Lowest



Conclusions

What we achieved in this first calibration step

- Built a per-pixel charge calibration for APTS Chip ID 27 (15×15 μm, N-gap).
- Derived a smooth Amplitude to e^- mapping using a high-correlation empirical fit $e^- = S \times (p_0(x - x_0) + p_1|x - x_0|^{0.5}) \times (p_2x + p_3)$ (per pixel).
- Pixel behaviors are consistent: all curves overlap closely; only a small spread remains.
- Example spread at a fixed amplitude (~10 k ADC units): $\approx 250 e^-$ between highest and lowest pixel.

Next steps

- Clustering & efficiency studies on the calibrated data.
- Spatial resolution vs. charge sharing.
- Compare with simulations
- Progress on the test-beam studies

Bibliography

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Thank you